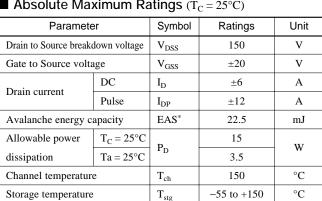
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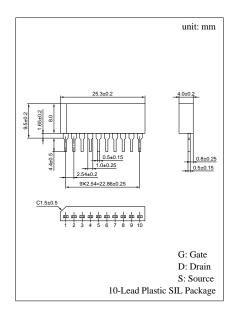
## Silicon N-Channel Power F-MOS FET

- Features
- Avalanche energy capacity guaranteed
- High-speed switching
- Low ON-resistance
- No secondary breakdown
- Low-voltage drive
- Applications
- Contactless relay
- Diving circuit for a solenoid
- Driving circuit for a motor
- Control equipment
- Switching power supply

#### ■ Absolute Maximum Ratings $(T_C = 25^{\circ}C)$

Parameter		Symbol	Ratings	Unit	
Drain to Source breakdown voltage		V <sub>DSS</sub>	150	V	
Gate to Source voltage		V <sub>GSS</sub>	±20	V	
Drain current	DC	$I_D$	±6	A	
	Pulse	$I_{\mathrm{DP}}$	±12	A	
Avalanche energy capacity		EAS*	22.5	mJ	
Allowable power	$T_C = 25^{\circ}C$	D	15	W	
dissipation	Ta = 25°C	$P_{\rm D}$	3.5		
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature		$T_{stg}$	-55 to +150	°C	



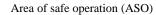


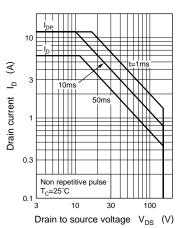
#### ■ Electrical Characteristics $(T_C = 25^{\circ}C)$

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I <sub>DSS</sub>	$V_{DS} = 120V, V_{GS} = 0$			10	μΑ
Gate to Source leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0$			±1	μΑ
Drain to Source breakdown voltage	V <sub>DSS</sub>	$I_D = 1 \text{mA}, V_{GS} = 0$	150			V
Gate threshold voltage	V <sub>th</sub>	$V_{DS} = 10V, I_D = 1mA$	1		2.5	V
Drain to Source ON-resistance	R <sub>DS(on)1</sub>	$V_{GS} = 10V, I_D = 3A$		0.42	0.6	Ω
	R <sub>DS(on)2</sub>	$V_{GS} = 4V$ , $I_D = 3A$		0.5	0.7	Ω
Forward transfer admittance	Y <sub>fs</sub>	$V_{DS} = 10V, I_D = 3A$	3	5.3		S
Diode forward voltage	V <sub>DSF</sub>	$I_{DR} = 3A, V_{GS} = 0$			-1.7	V
Input capacitance (Common Source)	C <sub>iss</sub>			620		pF
Output capacitance (Common Source)	C <sub>oss</sub>	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		120		pF
Reverse transfer capacitance (Common Source)	C <sub>rss</sub>			35		pF
Turn-on time (delay time)	t <sub>d(on)</sub>			10		ns
Rise time	t <sub>r</sub>	$V_{GS} = 10V, I_D = 3A$		30		ns
Fall time	t <sub>f</sub>	$V_{DD} = 100V, R_L = 33.3\Omega$		85		ns
Turn-off time (delay time)	$t_{d(off)}$			290		ns

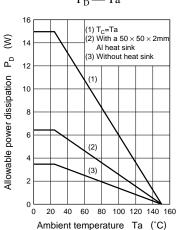
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<sup>\*</sup> L = 5mH,  $I_L = 3A$ , 1 pulse

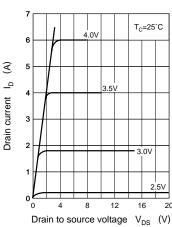




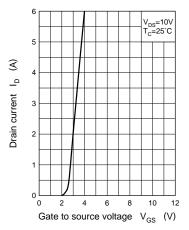




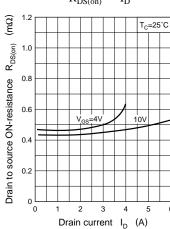
$$I_D - V_{DS}$$







### $R_{DS(on)} -\!\!\!\!- I_D$



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